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TLV61220

SLVSB53A - MAY 2012 - REVISED DECEMBER 2014

# TLV61220 Low-Input Voltage Step-Up Converter in Thin SOT-23 Package

Technical

Documents

## 1 Features

- Up to 95% Efficiency at Typical Operating Conditions
- 5.5-µA Quiescent Current
- Startup Into Load at 0.7-V Input Voltage
- Operating Input Voltage from 0.7 V to 5.5 V
- Pass-Through Function during Shutdown
- Minimum Switching Current 200 mA
- Protections:
  - Output Overvoltage
  - Overtemperature
  - Input Undervoltage Lockout
- Adjustable Output Voltage from 1.8 V to 5.5 V
- Small 6-pin Thin SOT-23 Package

## 2 Applications

- Battery Powered Applications
  - 1 to 3 Cell Alkaline, NiCd or NiMH
  - 1 Cell Li-Ion or Li-Primary
- Solar or Fuel Cell Powered Applications
- Consumer and Portable Medical Products
- Personal Care Products
- White or Status LEDs
- Smartphones

## **4** Typical Application Schematic

## 3 Description

Tools &

Software

The TLV61220 device provides a power-supply solution for products powered by either a single-cell, two-cell, or three-cell alkaline, NiCd or NiMH, or one-cell Li-lon or Li-polymer battery. Possible output currents depend on the input-to-output voltage ratio. The boost converter is based on a hysteretic controller topology using synchronous rectification to obtain maximum efficiency at minimal quiescent currents. The output voltage of the adjustable version can be programmed by an external resistor divider, or is set internally to a fixed output voltage. The converter can be switched off by a featured enable pin. While being switched off, battery drain is minimized. The device is packaged in a 6-pin thin SOT-23 package (DBV).

Support &

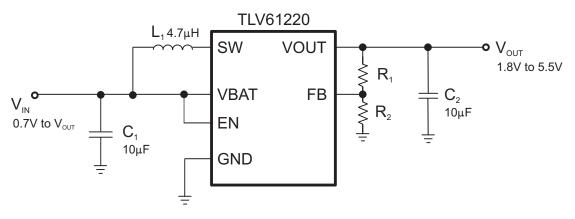
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#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)	
TLV61220	SOT (6)	2.90 mm x 1.60 mm	

(1) For all available packages, see the orderable addendum at the end of the datasheet.



2

# **Table of Contents**

1	Feat	tures	1					
2	Арр	Applications 1						
3	Des	cription	1					
4	Турі	ical Application Schematic	1					
5	Revi	ision History	2					
6	Devi	ice Options	3					
7	Pin	Configuration and Functions	3					
8	Spe	cifications	4					
	8.1	Absolute Maximum Ratings	4					
	8.2	ESD Ratings	4					
	8.3	Recommended Operating Conditions	4					
	8.4	Thermal Information	4					
	8.5	Electrical Characteristics	5					
	8.6	Typical Characteristics	6					
9	Para	ameter Measurement Information	9					
10	Deta	ailed Description	10					
	10.1							
	10.2	Functional Block Diagram	10					

11	Appl	lication and Implementation12
	11.1	Application Information 12
	11.2	Typical Application 12
12	Pow	er Supply Recommendations 16
13	Layo	out
	13.1	Layout Guidelines 16
	13.2	Layout Example 16
	13.3	Thermal Considerations 16
14	Devi	ce and Documentation Support 17
	14.1	Device Support 17
	14.2	Documentation Support 17
	14.3	Trademarks 17
	14.4	Electrostatic Discharge Caution 17
	14.5	Glossary 17
15	Mecl	hanical, Packaging, and Orderable
	Infor	mation 17

10.3 Feature Description..... 10 10.4 Device Functional Modes..... 11

## 5 Revision History

Changes from Original (May 2012) to Revision A

Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section ......1

#### EXAS STRUMENTS

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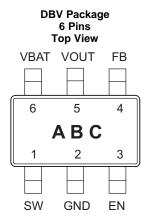
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## 6 Device Options

T <sub>A</sub>	OUTPUT VOLTAGE DC/DC	PACKAGE	PART NUMBER	
–40°C to 85°C	Adjustable	6-Pin SOT-23	TLV61220DBV	

## 7 Pin Configuration and Functions



#### **Pin Functions**

PIN		I/O	DESCRIPTION	
NAME	NO.	1/0	DESCRIPTION	
EN	3	Ι	Enable input (VBAT enabled, GND disabled)	
FB	4	Ι	Voltage feedback for programming the output voltage	
GND	2	I	IC ground connection for logic and power	
SW	1	I	Boost and rectifying switch input	
VBAT	6	Ι	Supply voltage	
VOUT	5	0	Boost converter output	

## 8 Specifications

## 8.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) <sup>(1)</sup>

		MIN	MAX	UNIT
V <sub>IN</sub>	Input voltage on VBAT, SW, VOUT, EN, FB	-0.3	7.5	V
TJ	Operating junction temperature	-40	150	°C
T <sub>stg</sub>	Storage temperature	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 8.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1500	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## 8.3 Recommended Operating Conditions

		MIN	NOM MAX	UNIT
V <sub>IN</sub>	Supply voltage at VIN	0.7	5.5	V
T <sub>A</sub>	Operating free air temperature range	-40	85	°C
TJ	Operating virtual junction temperature range	-40	125	°C

### 8.4 Thermal Information

		TLV61220	
	THERMAL METRIC <sup>(1)</sup>	DBV	UNIT
		6 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	185.7	
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	124.3	
$R_{\theta JB}$	Junction-to-board thermal resistance	31.3	°C/W
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	22.9	°C/VV
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	30.8	
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

#### 8.5 Electrical Characteristics

over recommended free-air temperature range and over recommended input voltage range (typical at an ambient temperature range of 25°C) (unless otherwise noted)

PARAMETER			TEST CONDITIONS	MIN	TYP	MAX	UNIT
DC/DC ST	AGE						
V <sub>IN</sub>	Input voltage range			0.7		5.5	V
V <sub>IN</sub>	Minimum input voltage	at startup	$R_{Load} \ge 150 \Omega$			0.7	V
V <sub>OUT</sub>	TLV61220 output volta	age range	V <sub>IN</sub> < V <sub>OUT</sub>	1.8		5.5	V
V <sub>FB</sub>	TLV61220 feedback vo	oltage		483	500	513	mV
I <sub>LH</sub>	Inductor current ripple				200		mA
			$V_{OUT}$ = 3.3 V, $V_{IN}$ = 1.2 V, $T_A$ = 25 $^\circ C$	220	400		mA
I <sub>SW</sub>	switch current limit		$V_{OUT}$ = 3.3 V, $T_A$ = -40°C to 85 °C	180	400		mA
			$V_{OUT}$ = 3.3 V, $T_A$ = 0°C to 85 °C	200	400		mA
	Rectifying switch on re	sistance,	V <sub>OUT</sub> = 3.3 V		1000		mΩ
	HSD		V <sub>OUT</sub> = 5 V		700		mΩ
R <sub>DS(on)</sub>			V <sub>OUT</sub> = 3.3 V		600		mΩ
	Main switch on resista	nce, LSD	V <sub>OUT</sub> = 5 V		550		mΩ
	Line regulation		V <sub>IN</sub> < V <sub>OUT</sub>		0.5%		
	Load regulation		V <sub>IN</sub> < V <sub>OUT</sub>		0.5%		
l <sub>Q</sub>	Quiescent V <sub>IN</sub>				0.5	0.9	μA
	current V <sub>OU</sub>	т	$I_{O} = 0 \text{ mA}, V_{EN} = V_{IN} = 1.2 \text{ V}, V_{OUT} = 3.3 \text{ V}$		5	7.5	μA
I <sub>SD</sub>	Shutdown current V <sub>IN</sub>		$V_{\text{EN}} = 0 \text{ V}, \text{ V}_{\text{IN}} = 1.2 \text{ V}, \text{ V}_{\text{OUT}} \ge \text{V}_{\text{IN}}$		0.2	0.5	μA
	Leakage current into V	/OUT	V <sub>EN</sub> = 0 V, V <sub>IN</sub> = 1.2 V, V <sub>OUT</sub> = 3.3 V		1		μA
I <sub>LKG</sub>	Leakage current into S	SW	$V_{EN} = 0 \text{ V}, \text{ V}_{IN} = 1.2 \text{ V}, \text{ V}_{SW} = 1.2 \text{ V}, \text{ V}_{OUT} \ge \text{ V}_{IN}$		0.01	0.2	μA
I <sub>FB</sub>	TLV61220 Feedback ir current	nput	V <sub>FB</sub> = 0.5 V		0.01		μA
I <sub>EN</sub>	EN input current		Clamped on GND or V <sub>IN</sub> (V <sub>IN</sub> < 1.5 V)		0.005	0.1	μA
CONTRO	STAGE		·				
V <sub>IL</sub>	EN input low voltage		V <sub>IN</sub> ≤ 1.5 V			0.2 × V <sub>IN</sub>	V
V <sub>IH</sub>	EN input high voltage		V <sub>IN</sub> ≤ 1.5 V	0.8 × V <sub>IN</sub>			V
V <sub>IL</sub>	EN input low voltage		5 V > V <sub>IN</sub> > 1.5 V			0.4	V
V <sub>IH</sub>	EN input high voltage		5 V > V <sub>IN</sub> > 1.5 V	1.2			V
V <sub>UVLO</sub>	Undervoltage lockout t for turn off	hreshold	V <sub>IN</sub> decreasing		0.5	0.7	V
	Overvoltage protection	threshold		5.5		7.5	V
	Overtemperature prote	ection			140		°C
	Overtemperature hyste	eresis			20		°C

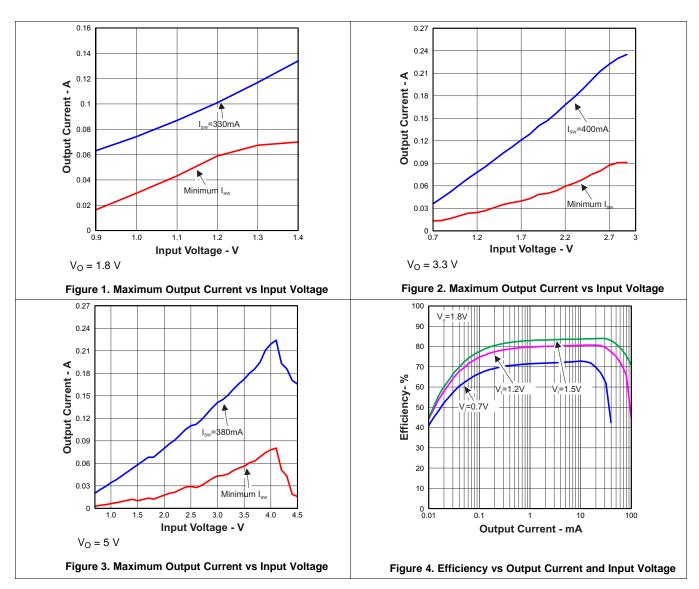
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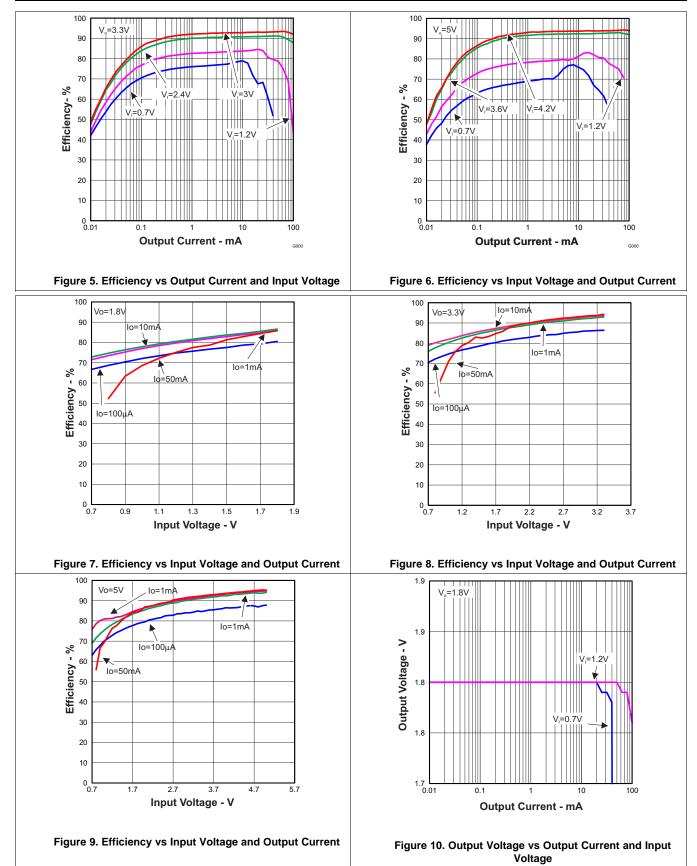
## 8.6 Typical Characteristics

## Table 1. Table of Graphs

		FIGURE
	Input Voltage, $I_{SW}$ = 330 mA, Minimum $I_{SW}$ = 200 mA, $V_O$ = 1.8V	Figure 1
Output Current	Input Voltage, $I_{SW}$ = 400 mA, Minimum $I_{SW}$ = 200 mA, $V_O$ = 3.3V	Figure 2
	Input Voltage, $I_{SW}$ = 380 mA, Minimum $I_{SW}$ = 200 mA, $V_O$ = 5V	Figure 3
	vs Output Current, V <sub>O</sub> = 1.8 V, V <sub>I</sub> = [0.7 V; 1.2 V; 1.5 V]	Figure 4
Efficiency	vs Output Current, V <sub>O</sub> = 3.3 V, V <sub>I</sub> = [0.7 V; 1.2 V; 2.4V; 3V]	Figure 5
	vs Output Current, V <sub>O</sub> = 5 V, V <sub>I</sub> = [0.7 V; 1.2 V; 3.6V; 4.2V]	Figure 6
	vs Input Voltage, V <sub>O</sub> = 1.8 V, I <sub>O</sub> = [100µA; 1mA ; 10mA; 50mA]	Figure 7
Efficiency	vs Input Voltage, $V_0 = 3.3 \text{ V}$ , $I_0 = [100 \mu\text{A}; 1\text{mA}; 10\text{mA}; 50\text{mA}]$	Figure 8
	vs Input Voltage, V <sub>O</sub> = 5 V, I <sub>O</sub> = [100µA; 1mA ; 10mA; 50mA]	Figure 9
	vs Output Current, V <sub>O</sub> = 1.8 V, V <sub>I</sub> = [0.7 V; 1.2 V]	Figure 10
Output Voltage	vs Output Current, V <sub>O</sub> = 3.3 V, V <sub>I</sub> = [0.7 V; 1.2 V; 2.4 V]	Figure 11

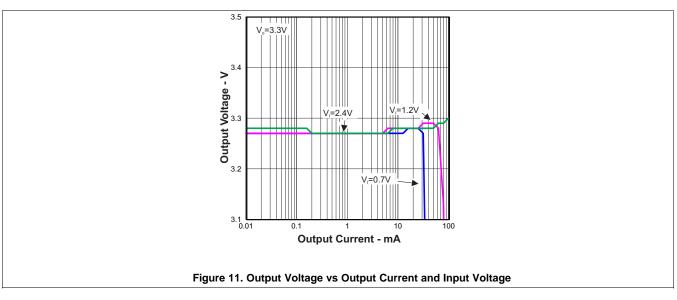








TLV61220 SLVSB53A-MAY 2012-REVISED DECEMBER 2014





## 9 Parameter Measurement Information

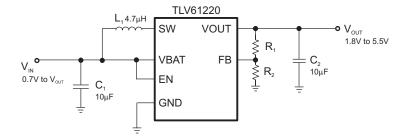


Figure 12. Parameter Measurement Schematic

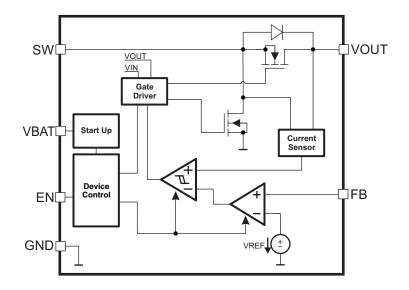


## **10** Detailed Description

#### 10.1 Overview

The TLV61220 is a high performance, highly efficient boost converter. To achieve high efficiency the power stage is realized as a synchronous boost topology. For the power switching two actively controlled low  $R_{DS(on)}$  power MOSFETs are implemented.

### **10.2 Functional Block Diagram**



### **10.3 Feature Description**

#### 10.3.1 Controller Circuit

The device is controlled by a hysteretic current mode controller. This controller regulates the output voltage by keeping the inductor ripple current constant in the range of 200 mA and adjusting the offset of this inductor current depending on the output load. In case the required average input current is lower than the average inductor current defined by this constant ripple the inductor current gets discontinuous to keep the efficiency high at low load conditions.

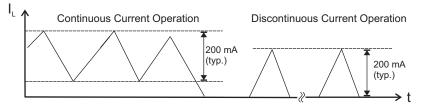


Figure 13. Hysteretic Current Operation

The output voltage  $V_{OUT}$  is monitored via the feedback network which is connected to the voltage error amplifier. To regulate the output voltage, the voltage error amplifier compares this feedback voltage to the internal voltage reference and adjusts the required offset of the inductor current accordingly. An external resistor divider needs to be connected.

The self oscillating hysteretic current mode architecture is inherently stable and allows fast response to load variations. It also allows using inductors and capacitors over a wide value range.



#### Feature Description (continued)

#### 10.3.1.1 Startup

After the EN pin is tied high, the device starts to operate. In case the input voltage is not high enough to supply the control circuit properly a startup oscillator starts to operate the switches. During this phase the switching frequency is controlled by the oscillator and the maximum switch current is limited. As soon as the device has built up the output voltage to about 1.8 V, high enough for supplying the control circuit, the device switches to its normal hysteretic current mode operation. The startup time depends on input voltage and load current.

#### 10.3.1.2 Operation at Output Overload

If in normal boost operation the inductor current reaches the internal switch current limit threshold the main switch is turned off to stop further increase of the input current.

In this case the output voltage will decrease since the device can not provide sufficient power to maintain the set output voltage.

If the output voltage drops below the input voltage the backgate diode of the rectifying switch gets forward biased and current starts flow through it. This diode cannot be turned off, so the current finally is only limited by the remaining DC resistances. As soon as the overload condition is removed, the converter resumes providing the set output voltage.

#### 10.3.1.3 Undervoltage Lockout

An implemented undervoltage lockout function stops the operation of the converter if the input voltage drops below the typical undervoltage lockout threshold. This function is implemented in order to prevent malfunctioning of the converter.

#### 10.3.1.4 Overvoltage Protection

If, for any reason, the output voltage is not fed back properly to the input of the voltage amplifier, control of the output voltage will not work anymore. Therefore an overvoltage protection is implemented to avoid the output voltage exceeding critical values for the device and possibly for the system it is supplying. For this protection the TLV61220 output voltage is also monitored internally. In case it reaches the internally programmed threshold of 6.5 V typically the voltage amplifier regulates the output voltage to this value.

If the TLV61220 is used to drive LEDs, this feature protects the circuit if the LED fails.

#### 10.3.1.5 Overtemperature Protection

The device has a built-in temperature sensor which monitors the internal IC junction temperature. If the temperature exceeds the programmed threshold (see electrical characteristics table), the device stops operating. As soon as the IC temperature has decreased below the programmed threshold, it starts operating again. To prevent unstable operation close to the region of overtemperature threshold, a built-in hysteresis is implemented.

#### **10.4 Device Functional Modes**

#### 10.4.1 Device Enable and Shutdown Mode

The device is enabled when EN is set high and shut down when EN is low. During shutdown, the converter stops switching and all internal control circuitry is turned off. In this case the input voltage is connected to the output through the back-gate diode of the rectifying MOSFET. This means that there always will be voltage at the output which can be as high as the input voltage or lower depending on the load.

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## **11** Application and Implementation

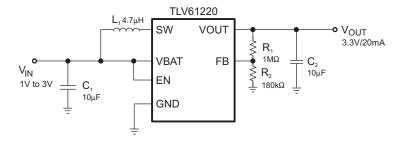
#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### **11.1** Application Information

The TLV61220 is intended for systems powered by a single cell battery to up to three Alkaline, NiCd or NiMH cells with a typical terminal voltage between 0.7 V and 5.5 V. It can also be used in systems powered by one-cell Li-Ion or Li-Polymer batteries with a typical voltage between 2.5 V and 4.2 V. Additionally, any other voltage source with a typical output voltage between 0.7 V and 5.5 V can be used with the TLV61220.

### **11.2 Typical Application**



## Figure 14. Typical Application Circuit for Adjustable Output Voltage Option

#### 11.2.1 Design Requirements

In this example, TLV61220 is used to design a 3.3-V power supply with up to 50-mA output current capability. The TLV61220 can be powered by a single-cell battery to up to three Alkaline, NiCd or NiMH cells with a typical terminal voltage between 0.7 V and 5.5 V. It can also be used in systems powered by one-cell Li-lon or Li-Polymer batteries with a typical voltage between 2.5 V and 4.2 V. In this example, the input voltage range is from 2 V to 3 V for one-cell coin cell battery input design.

PARAMETERS	VALUES
Input Voltage	2 V to 3 V
Output Voltage	3.3 V
Output Current	50 mA

#### Table 2. TLV61220 3.3 V Output Design Requirements

#### 11.2.2 Detailed Design Procedure

COMPONENT REFERENCE	PART NUMBER	MANUFACTURER	VALUE
C <sub>1</sub>	GRM188R60J106ME84D	Murata	10 µF, 6.3V. X5R Ceramic
C <sub>2</sub>	GRM188R60J106ME84D	Murata	10 µF, 6.3V. X5R Ceramic
L <sub>1</sub>	1269AS-H-4ZR7N	Toko	4.7 μH
R <sub>1</sub> , R <sub>2</sub>			$R_1\text{=}1M\Omega,R_2\text{=}$ Values depending on the programmed output voltage



#### 11.2.2.1 Adjustable Output Voltage Version

An external resistor divider is used to adjust the output voltage. The resistor divider needs to be connected between VOUT, FB and GND as shown in Figure 14. When the output voltage is regulated properly, the typical voltage value at the FB pin is 500 mV. The maximum recommended value for the output voltage is 5.5 V. The current through the resistive divider should be about 100 times greater than the current into the FB pin. The typical current into the FB pin is 0.01  $\mu$ A, and the voltage across the resistor between FB and GND, R<sub>2</sub>, is typically 500 mV. Based on those two values, the recommended value for R<sub>2</sub> should be lower than 500 k $\Omega$ , in order to set the divider current to 1  $\mu$ A or higher. The value of the resistor connected between VOUT and FB, R<sub>1</sub>, depending on the needed output voltage (V<sub>OUT</sub>), can be calculated using Equation 1:

$$R_1 = R_2 x \left( \frac{V_{OUT}}{V_{FB}} - 1 \right)$$
(1)

As an example, if an output voltage of 3.3 V is needed, a 1-M $\Omega$  resistor is calculated for R<sub>1</sub> when for R<sub>2</sub> a 180-k $\Omega$  has been selected.

#### 11.2.2.2 Inductor Selection

To make sure that the TLV61220 can operate, a suitable inductor must be connected between pin VBAT and pin SW. Inductor values of 4.7 µH show good performance over the whole input and output voltage range .

Choosing other inductance values affects the switching frequency *f* proportional to 1/L as shown in Equation 2.

$$L = \frac{1}{f \times 200 \text{ mA}} \times \frac{V_{\text{IN}} \times (V_{\text{OUT}} - V_{\text{IN}})}{V_{\text{OUT}}}$$
(2)

Choosing inductor values higher than 4.7  $\mu$ H can improve efficiency due to reduced switching frequency and, therefore, with reduced switching losses. Using inductor values below 2.2  $\mu$ H is not recommended.

Having selected an inductance value, the peak current for the inductor in steady state operation can be calculated. Equation 3 gives the peak current estimate.

$$I_{L,MAX} = \begin{cases} \frac{V_{OUT} \times I_{OUT}}{0.8 \times V_{IN}} + 100 \text{ mA}; & \text{continous current operation} \\ 200 \text{ mA}; & \text{discontinuous current operation} \end{cases}$$
(3)

For selecting the inductor this would be the suitable value for the current rating. It also needs to be taken into account that load transients and error conditions may cause higher inductor currents.

Equation 4 helps to estimate whether the device will work in continuous or discontinuous operation depending on the operating points. As long as the inequation is true, continuous operation is typically established. If the inequation becomes false, discontinuous operation is typically established.

$$\frac{V_{\text{out}} \times I_{\text{out}}}{V_{\text{IN}}} > 0.8 \times 100 \text{ mA}$$

(4)

The following inductor series from different suppliers have been used with TLV61220 converters:

	·				
VENDOR	INDUCTOR SERIES				
Toko	DFE252010C				
Cailanaft	EPL3015				
Coilcraft	EPL2010				
Murata	LQH3NP				
Taiyo Yuden	NR3015				
Wurth Elektronik	WE-TPC Typ S				

#### Table 4. List of Inductors

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#### 11.2.2.3 Capacitor Selection

#### 11.2.2.3.1 Input Capacitor

At least a 10-µF input capacitor is recommended to improve transient behavior of the regulator and EMI behavior of the total power supply circuit. A ceramic capacitor placed as close as possible to the VBAT and GND pins of the IC is recommended.

#### 11.2.2.3.2 Output Capacitor

For the output capacitor  $C_2$ , it is recommended to use small ceramic capacitors placed as close as possible to the VOUT and GND pins of the IC. If, for any reason, the application requires the use of large capacitors which can not be placed close to the IC, the use of a small ceramic capacitor with an capacitance value of around 2.2µF in parallel to the large one is recommended. This small capacitor should be placed as close as possible to the VOUT and GND pins of the IC.

A minimum capacitance value of 4.7  $\mu$ F should be used, 10  $\mu$ F are recommended. If the inductor value exceeds 4.7  $\mu$ H, the value of the output capacitance value needs to be half the inductance value or higher for stability reasons, see Equation 5.

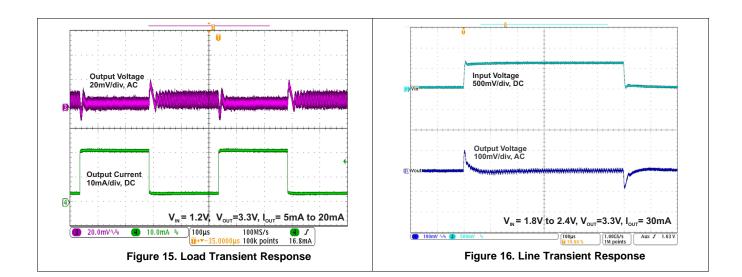
$$C_2 \ge \frac{L}{2} \times \frac{\mu F}{\mu H}$$

(5)

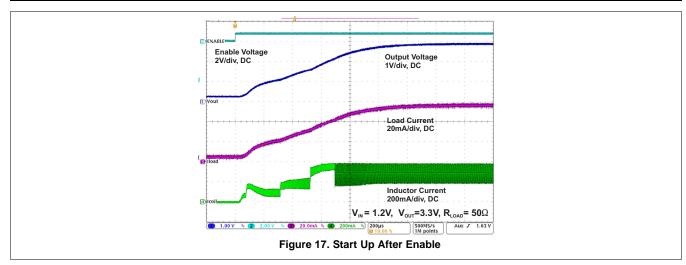
The TLV61220 is not sensitive to the ESR in terms of stability. Using low ESR capacitors, such as ceramic capacitors, is recommended anyway to minimize output voltage ripple. If heavy load changes are expected, the output capacitor value should be increased to avoid output voltage drops during fast load transients.

#### 11.2.3 Application Curves

	FIGURE
Load transient, $V_I = 1.2$ V, $V_O = 3.3$ V, $I_O = 5$ mA to 20 mA	Figure 15
Line transient, V <sub>I</sub> = 1.8 V to 2.4V, V <sub>O</sub> = 3.3 V, I <sub>O</sub> = 30 mA	Figure 16
Startup after Enable, $V_I$ = 1.2 V, $V_O$ = 3.3 V, $R_{LOAD}$ = 50 $\Omega$	Figure 17









## **12 Power Supply Recommendations**

The power supply can be single-cell, two-cell, or three-cell alkaline, NiCd or NiMH, or one-cell Li-Ion or Lipolymer battery.

The input supply should be well regulated with the rating of TLV61220. If the input supply is located more than a few inches from the device, additional bulk capacitance may be required in addition to the ceramic bypass capacitors. An electrolytic or tantalum capacitor with a value of 47 µF is a typical choice.

## 13 Layout

#### 13.1 Layout Guidelines

As for all switching power supplies, the layout is an important step in the design, especially at high peak currents and high switching frequencies. If the layout is not carefully done, the regulator could show stability problems as well as EMI problems. Therefore, use wide and short traces for the main current path and for the power ground paths. The input and output capacitor, as well as the inductor should be placed as close as possible to the IC.

The feedback divider should be placed as close as possible to the control ground pin of the IC. To lay out the ground, it is recommended to use short traces as well, separated from the power ground traces. This avoids ground shift problems, which can occur due to superimposition of power ground current and control ground current. Assure that the ground traces are connected close to the device GND pin.

### 13.2 Layout Example

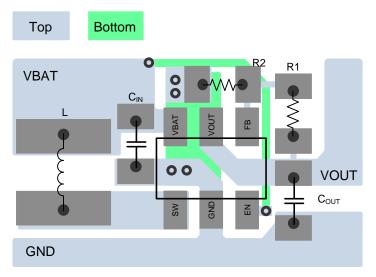


Figure 18. PCB Layout Recommendation

### **13.3 Thermal Considerations**

Implementation of integrated circuits in low-profile and fine-pitch surface-mount packages typically requires special attention to power dissipation. Many system-dependent issues such as thermal coupling, airflow, added heat sinks and convection surfaces, and the presence of other heat-generating components affect the power-dissipation limits of a given component.

Three basic approaches for enhancing thermal performance are listed below.

- Improving the power-dissipation capability of the PCB design
- Improving the thermal coupling of the component to the PCB
- Introducing airflow in the system

For more details on how to use the thermal parameters in the dissipation ratings table please check the *Thermal Characteristics Application Note* (SZZA017) and the *IC Package Thermal Metrics Application Note* (SPRA953).



## 14 Device and Documentation Support

### 14.1 Device Support

#### 14.1.1 Third-Party Products Disclaimer

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### 14.2 Documentation Support

#### 14.2.1 Related Documentation

For related documentation see the following:

- Thermal Characteristics Application Note, SZZA017
- IC Package Thermal Metrics Application Note, SPRA953

## 14.3 Trademarks

All trademarks are the property of their respective owners.

#### 14.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 14.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

## 15 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



6-Feb-2020

## **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TLV61220DBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VUAI	Samples
TLV61220DBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 85	VUAI	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

6-Feb-2020

# PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION





## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV61220DBVR	SOT-23	DBV	6	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TLV61220DBVT	SOT-23	DBV	6	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3

TEXAS INSTRUMENTS

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# PACKAGE MATERIALS INFORMATION

24-Apr-2020



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV61220DBVR	SOT-23	DBV	6	3000	180.0	180.0	18.0
TLV61220DBVT	SOT-23	DBV	6	250	180.0	180.0	18.0

# **DBV0006A**



# **PACKAGE OUTLINE**

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.2. This drawing is subject to change without notice.3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.

- 4. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation. 5. Refernce JEDEC MO-178.



# **DBV0006A**

# **EXAMPLE BOARD LAYOUT**

# SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# **DBV0006A**

# **EXAMPLE STENCIL DESIGN**

# SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



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